

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT MULTI CHIP

TD62M8600F

8CH LOW SATURATION VOLTAGE SOURCE DRIVER

TD62M8600F is Multi Chip IC incorporates 8 low saturation discrete transistors equipped Fly-wheeling Diode and Bias resistor.

This IC is suitable for a battery use motor drive and LED display module applications.

FEATURES

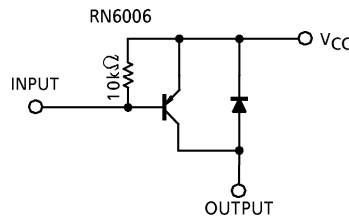
- Suitable for Motor drive circuit and LED display module
- Bias Resistor and Diodes are equipped : $R = 10k\Omega$
- Low Saturation Voltage

$$V_{CE(sat)} = 0.13V \text{ (Typ.) at } I_C = 1A$$

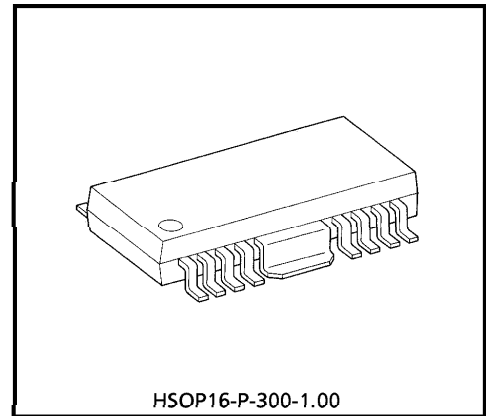
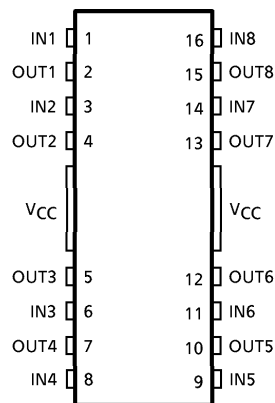
$$V_{CE(sat)} = 0.25V \text{ (Typ.) at } I_C = 2A$$

- HSOP16 pitch power small package sealed

SCHEMATICS



PIN CONNECTION (TOP VIEW)



Weight : 0.50g (Typ.)

961001EBA2

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MAXIMUM RATINGS (Ta = 25°C)

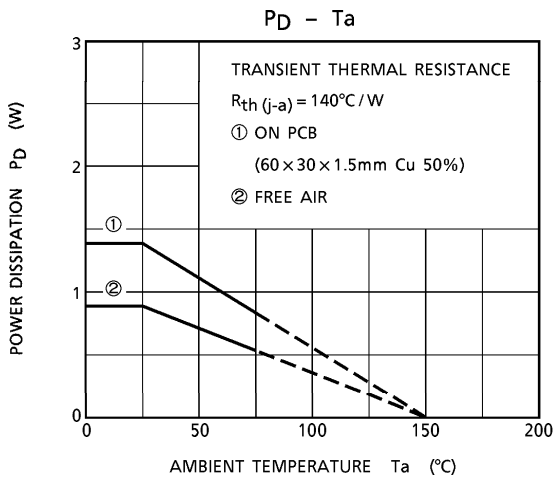
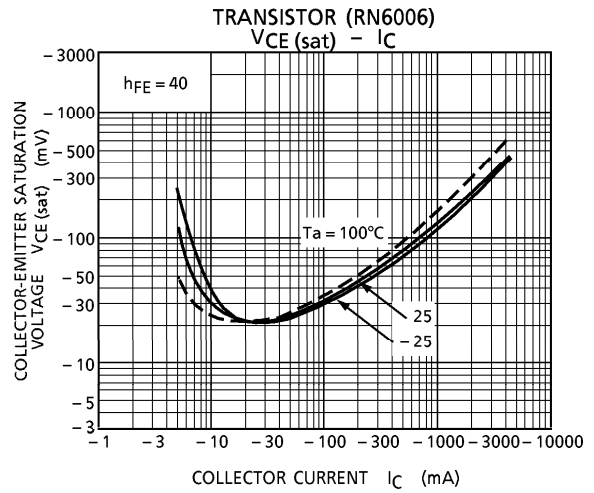
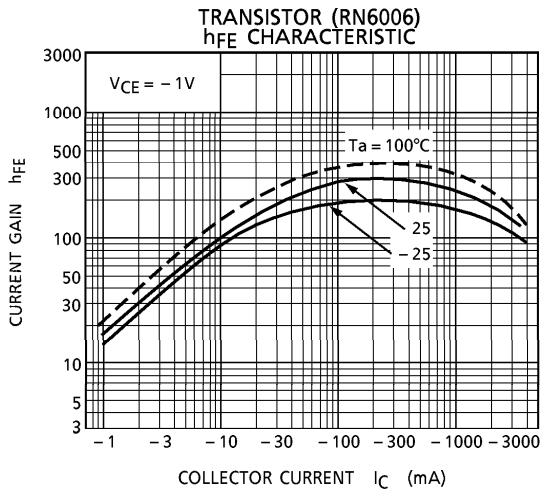
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	- 10	V
Breakdown Voltage	V _{CB0}	- 10	V
	V _{CER}	- 10	
	V _{EBO}	- 6	
Output Current	I _O	- 2	A / ch
	I _O (PEAK)	(Note 1) - 4	
Base Current	I _B (AVE)	- 0.4	A
	I _B (PEAK)	- 0.8	
Fly-wheeling Diode Forward Current	I _F	(Note 2) - 2	A
Power Dissipation	P _D	900	mW
Junction Temperature	T _j	150	°C
Operating Temperature	T _{opr}	- 40~85	°C
Storage Temperature	T _{stg}	- 55~150	°C

(Note 1) T = 10ms MAX. and maximum duty is less than 30%.

(Note 2) T = 10ms single pulse

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE} (1)	—	V _{CE} = - 1V, I _C = - 0.5A	160	—	600	—
	h _{FE} (2)	—	V _{CE} = - 1V, I _C = - 1.5A	60	130	—	
Saturation Voltage	V _{CE} (sat)	—	I _C = - 1A, I _B = - 25mA	—	- 0.13	- 0.25	V
			I _C = 2A, I _B = 50mA	—	- 0.25	- 0.50	
Transition Frequency	f _T	—	V _{CE} = - 2V, I _C = - 0.5A	—	150	—	MHz
Leakage Current	I _{OL}	—	V _{CC} = - 10V	—	0	- 10	μA
Fly-wheeling Diode Forward Voltage	V _F	—	I _F = - 300mA	—	- 0.89	- 1.2	V
			I _F = - 450mA, 10ms	—	- 1.60	—	
Base-Emitter Resistor	R _{BE}	—	—	7	10	13	kΩ
Base-Emitter Forward Voltage	V _{BE}	—	V _{CE} = - 1V, I _C = - 2.0A	—	- 0.84	- 1.5	V

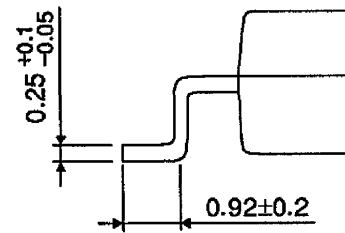
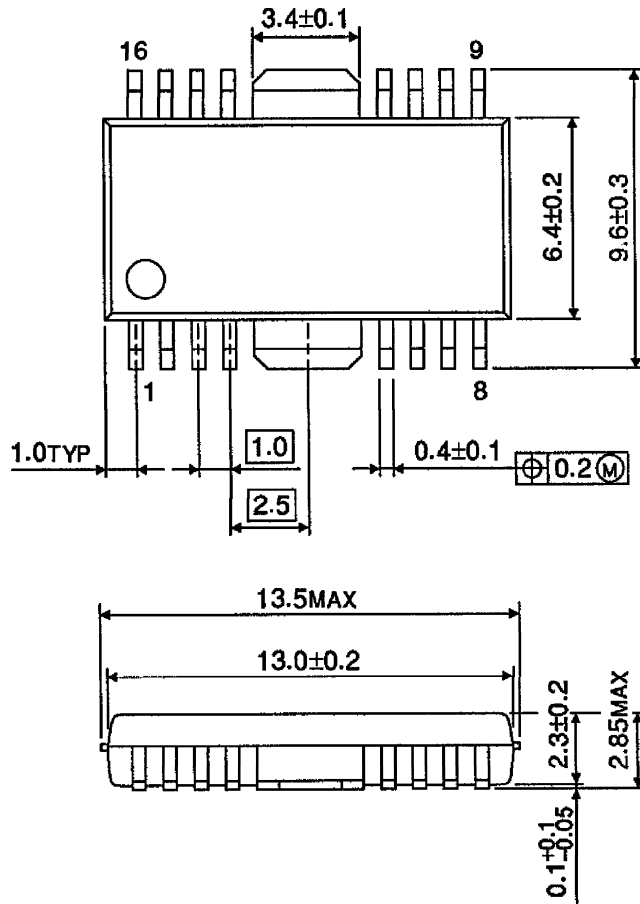


PRECAUTIONS for USING

Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

OUTLINE DRAWING
HSOP16-P-300-1.00

Unit : mm



Weight : 0.50g (Typ.)